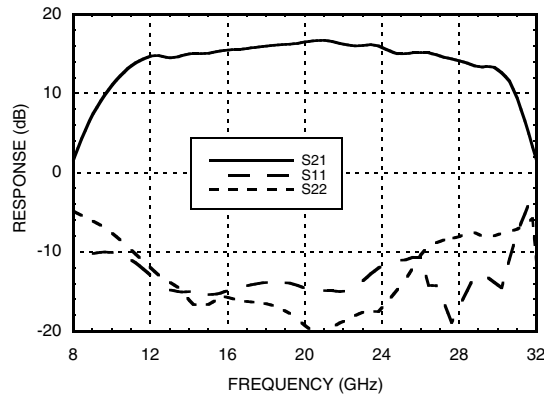


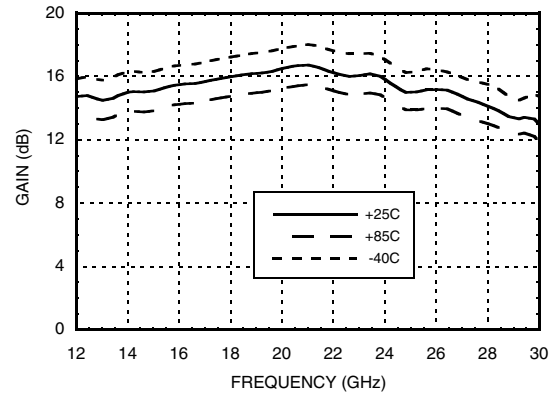


**GaAs PHEMT MMIC MEDIUM
POWER AMPLIFIER, 12 - 30 GHz**

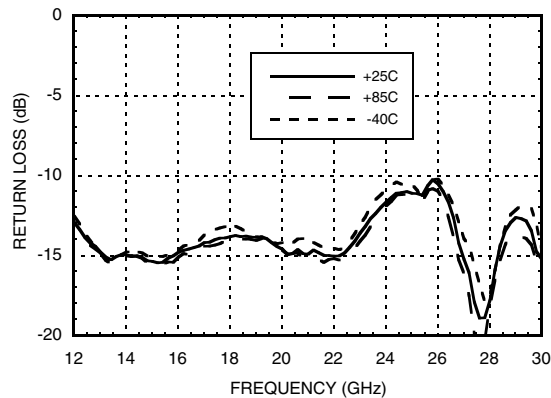
Broadband Gain & Return Loss



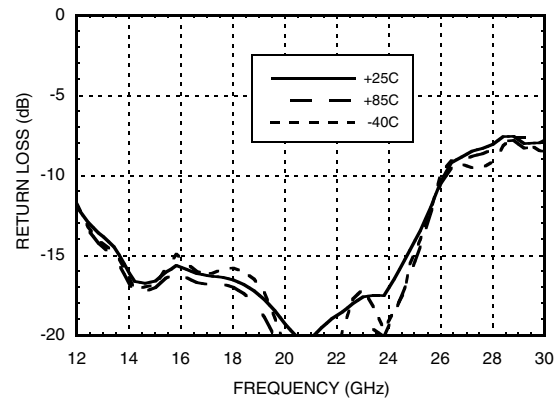
Gain vs. Temperature



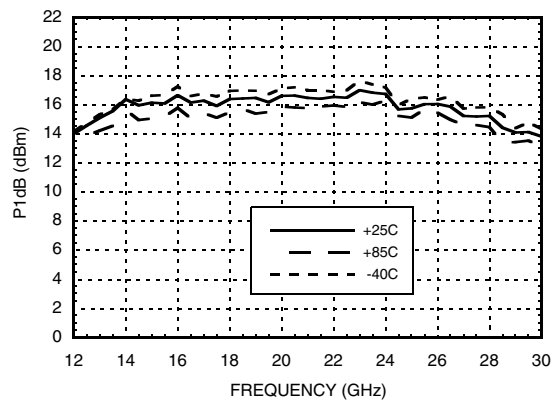
Input Return Loss vs. Temperature



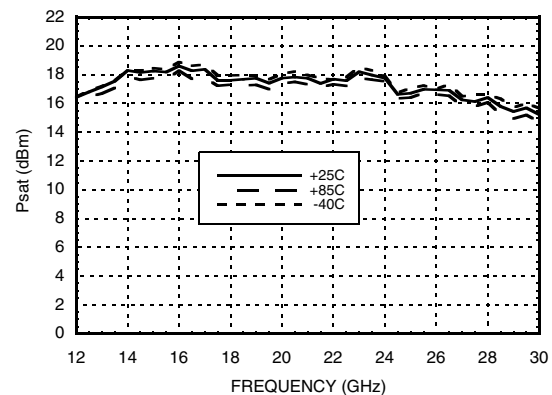
Output Return Loss vs. Temperature



P1dB vs. Temperature

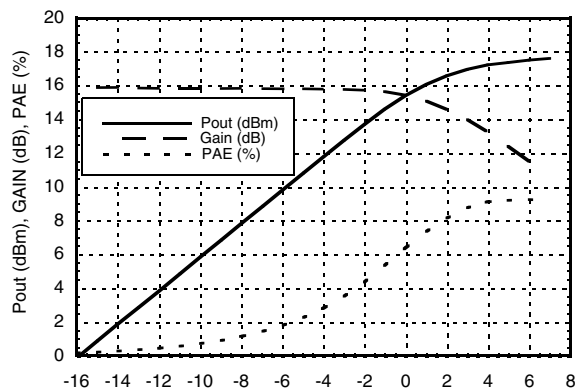
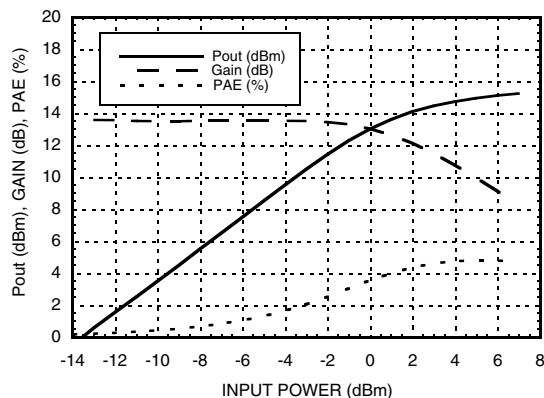
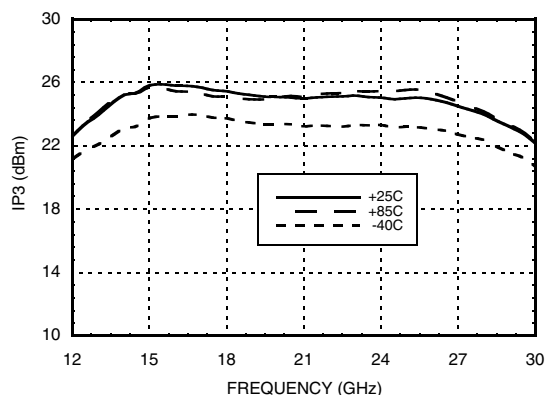
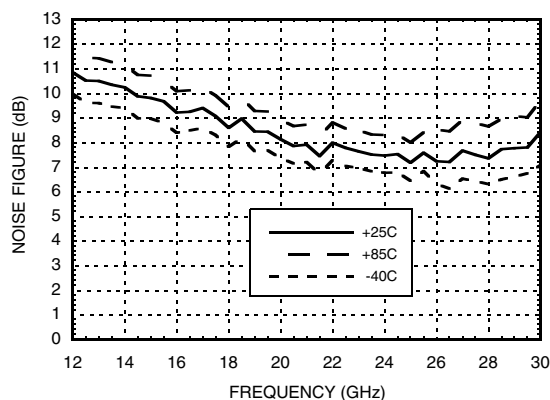
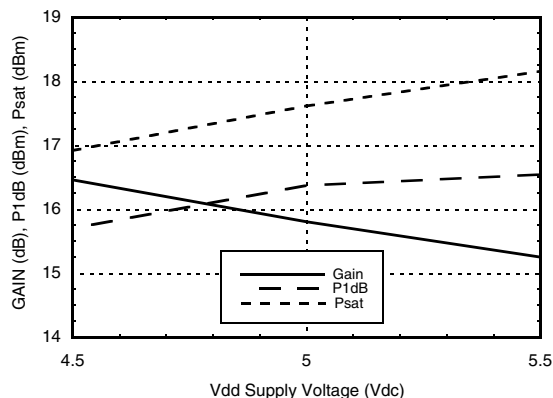
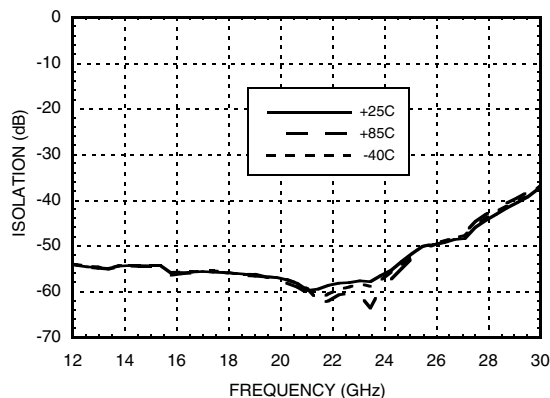


Psat vs. Temperature





GaAs PHEMT MMIC MEDIUM POWER AMPLIFIER, 12 - 30 GHz

Power Compression @ 18 GHz

Power Compression @ 30 GHz

Output IP3 vs. Temperature

Noise Figure vs. Temperature

Gain & Power vs. Supply Voltage @ 18 GHz

Reverse Isolation vs. Temperature




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Absolute Maximum Ratings

Drain Bias Voltage (Vdd)	+5.5 Vdc
RF Input Power (RFIN)(Vdd = +5Vdc)	+10 dBm
Channel Temperature	175 °C
Continuous Pdiss (T= 85 °C) (derate 10 mW/°C above 85 °C)	0.92 W
Thermal Resistance (channel to ground paddle)	98 °C/W
Storage Temperature	-65 to +150 °C
Operating Temperature	-40 to +85 °C
ESD Sensitivity (HBM)	Class 1A

Typical Supply Current vs. Vdd

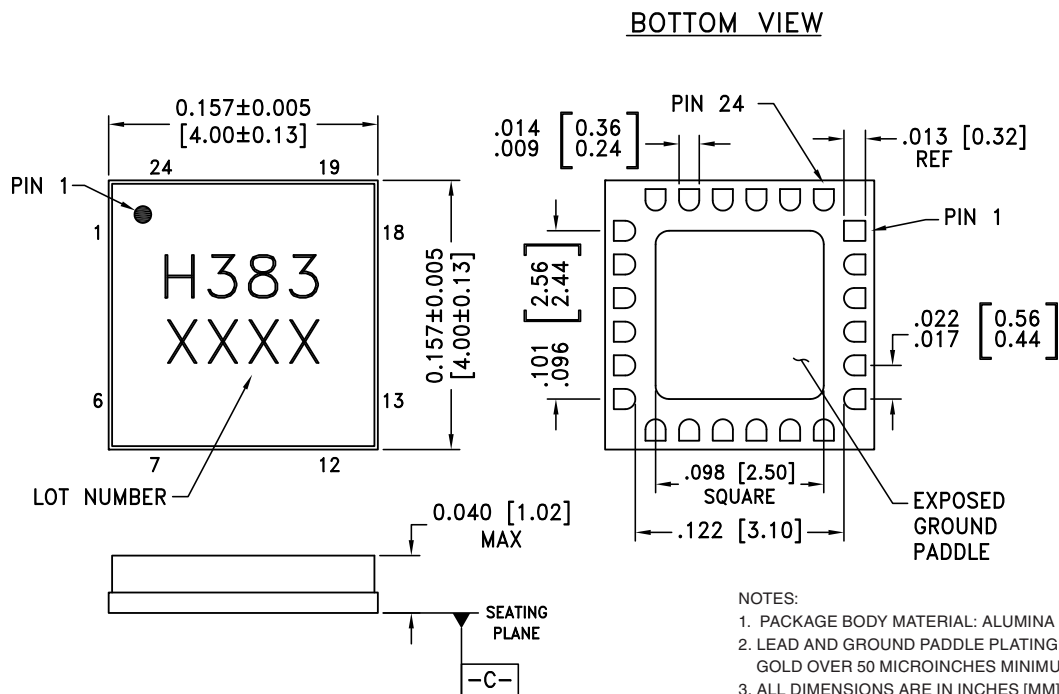
Vdd (V)	Idd (mA)
+4.5	99
+5.0	100
+5.5	101

Note: Amplifier will operate over full voltage ranges shown above



ELECTROSTATIC SENSITIVE DEVICE
OBSERVE HANDLING PRECAUTIONS

Outline Drawing



Package Information

Part Number	Package Body Material	Lead Finish	MSL Rating	Package Marking ^[2]
HMC383LC4	Alumina, White	Gold over Nickel	MSL3 ^[1]	H383 XXXX

[1] Max peak reflow temperature of 260 °C

[2] 4-Digit lot number XXXX

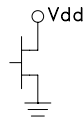
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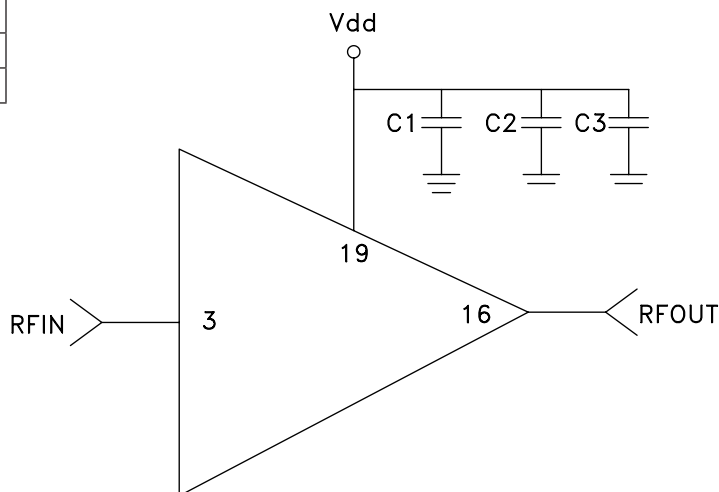
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Pin Descriptions

Pin Number	Function	Description	Interface Schematic
1, 2, 4 - 15, 17, 18, 20 - 24	N/C	No connection required. These pins may be connected to RF/DC ground without affecting performance if using grounded coplanar wave guide transmission lines.	
3	RFIN	This pad is AC coupled and matched to 50 Ohms.	RFIN — —
16	RFOUT	This pad is AC coupled and matched to 50 Ohms.	— — RFOUT
19	Vdd	Power Supply Voltage for the amplifier. External bypass capacitors of 100 pF, 1,000 pF and 2.2 μ F are required.	
	GND	Package base has an exposed metal ground that must be connected to RF/DC ground. Vias under the device are required	

Application Circuit

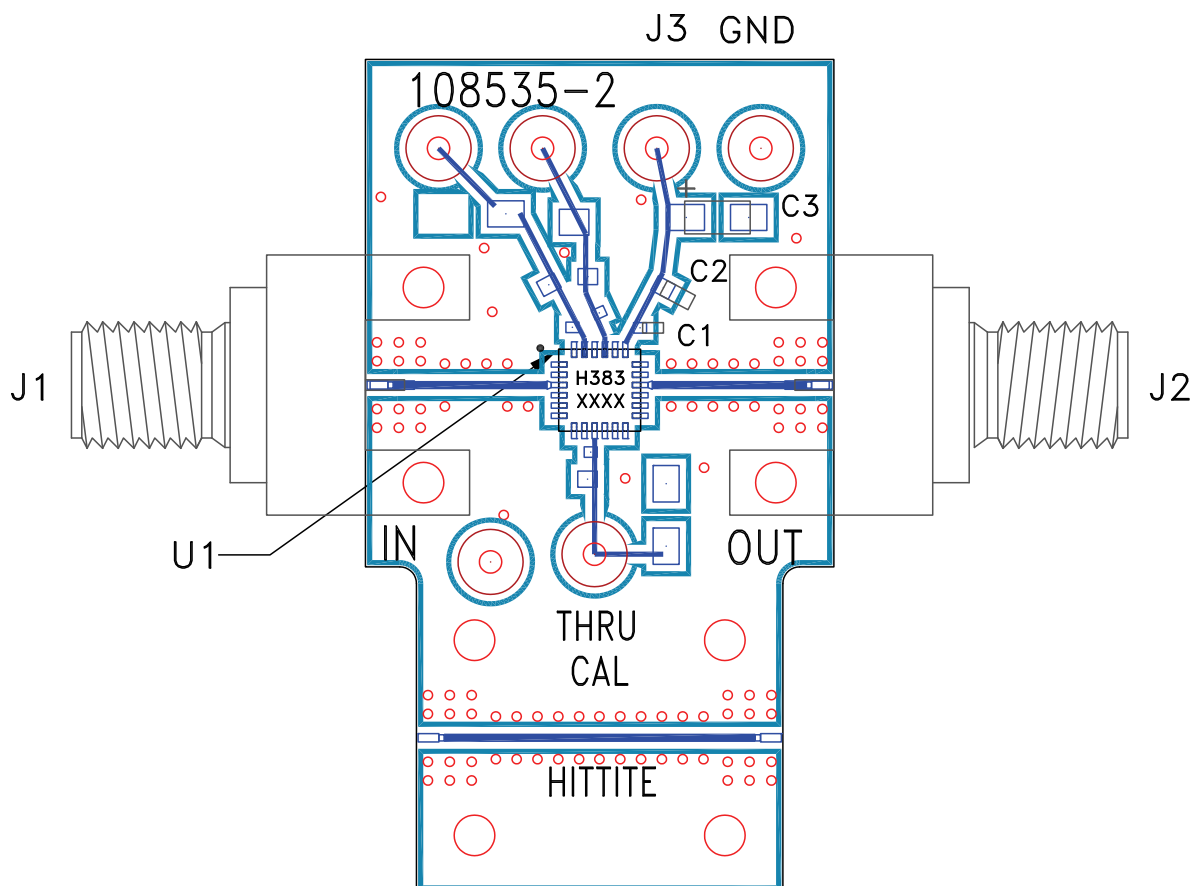
Component	Value
C1	100 pF
C2	1,000 pF
C3	2.2 μ F





**GaAs PHEMT MMIC MEDIUM
POWER AMPLIFIER, 12 - 30 GHz**

Evaluation PCB



List of Materials for Evaluation PCB 122198 ^[1]

Item	Description
J1, J2	2.92 mm PCB mount K-connector
J3, J4	DC Pin
C1	100 pF capacitor, 0402 pkg.
C2	1,000 pF Capacitor, 0603 pkg.
C3	2.2µF Capacitor, Tantalum
U1	HMC383LC4 Amplifier
PCB ^[2]	108535 Evaluation PCB

[1] Reference this number when ordering complete evaluation PCB

[2] Circuit Board Material: Rogers 4350.

The circuit board used in this application should use RF circuit design techniques. Signal lines should have 50 Ohm impedance while the package ground leads and exposed paddle should be connected directly to the ground plane similar to that shown. A sufficient number of via holes should be used to connect the top and bottom ground planes. The evaluation board should be mounted to an appropriate heat sink. The evaluation circuit board shown is available from Hittite upon request.